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FDG6308P

P-Channel 1.8V Specified PowerTrench® MOSFET

General Description

This P-Channel 1.8V specified MOSFET uses Fairchild's advanced low voltage PowerTrench process. It has been optimized for battery power management applications.

Applications

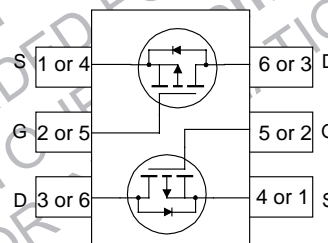- Battery management
- Load switch

Features

- −0.6 A, −20 V. $R_{DS(ON)} = 0.40\ \Omega$ @ $V_{GS} = -4.5$ V
  $R_{DS(ON)} = 0.55\ \Omega$ @ $V_{GS} = -2.5$ V
  $R_{DS(ON)} = 0.80\ \Omega$ @ $V_{GS} = -1.8$ V

- Low gate charge

- High performance trench technology for extremely low $R_{DS(ON)}$

- Compact industry standard SC70-6 surface mount package
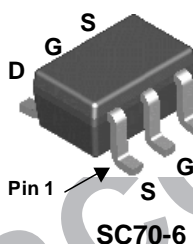
SC70-6

The pinouts are symmetrical; pin 1 and pin 4 are interchangeable.

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		−20	V
V_{GSS}	Gate-Source Voltage		± 8	V
I_D	Drain Current – Continuous	(Note 1)	−0.6	A
	– Pulsed		−1.8	
P_D	Power Dissipation for Single Operation	(Note 1)	0.3	W
T_J, T_{STG}	Operating and Storage Junction Temperature Range		−55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1)	415	°C/W

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.08	FDG6308P	7"	8mm	3000 units

Electrical Characteristics
$T_A = 25°C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0$ V, $I_D = -250$ µA	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250$ µA, Referenced to 25°C		-15		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -16$ V, $V_{GS} = 0$ V			-1	µA
I_{GSSF}	Gate–Body Leakage, Forward	$V_{GS} = -8$ V, $V_{DS} = 0$ V			-100	nA
I_{GSSR}	Gate–Body Leakage, Reverse	$V_{GS} = 8$ V, $V_{DS} = 0$ V			100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -250$ µA	-0.4	-0.9	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250$ µA, Referenced to 25°C		2		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5$ V, $I_D = -0.6$ A $V_{GS} = -2.5$ V, $I_D = -0.5$ A $V_{GS} = -1.8$ V, $I_D = -0.4$ A $V_{GS} = -4.5$ V, $I_D = -0.6$ A, $T_J=125°C$		0.27 0.36 0.55 0.35	0.40 0.55 0.80 0.56	Ω
$I_{D(on)}$	On–State Drain Current	$V_{GS} = -4.5$ V, $V_{DS} = -5$ V	-2			A
g_{FS}	Forward Transconductance	$V_{DS} = -5$ V, $I_D = -0.6$ A		2.1		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = -10$ V, $V_{GS} = 0$ V, f = 1.0 MHz		153		pF
C_{oss}	Output Capacitance			25		pF
C_{rss}	Reverse Transfer Capacitance			9		pF
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10$ V, $I_D = 1$ A, $V_{GS} = -4.5$ V, $R_{GEN} = 6$ Ω		5	10	ns
t_r	Turn–On Rise Time			15	27	ns
$t_{d(off)}$	Turn–Off Delay Time			7	14	ns
t_f	Turn–Off Fall Time			1.6	3.2	ns
Q_g	Total Gate Charge	$V_{DS} = -10$ V, $I_D = -0.6$ A, $V_{GS} = -4.5$ V		1.8	2.5	nC
Q_{gs}	Gate–Source Charge			0.3		nC
Q_{gd}	Gate–Drain Charge			0.4		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				-0.25	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0$ V, $I_S = -0.25$ A (Note 2)		-0.77	-1.2	V

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. $R_{\theta JA} = 415°C/W$ when mounted on a minimum pad.

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%
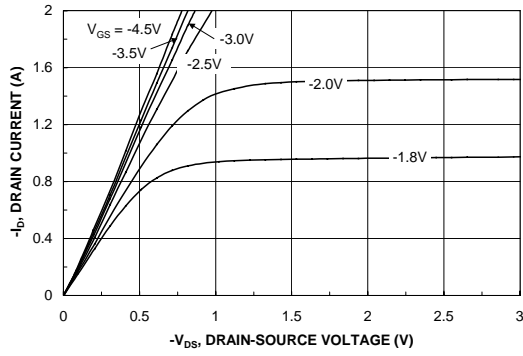
Typical Characteristics

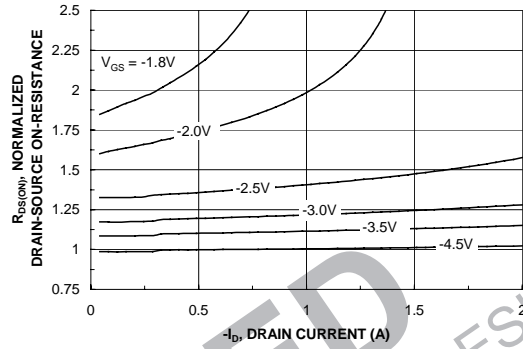
Figure 1. On-Region Characteristics.

Figure 2. On-Resistance Variation with
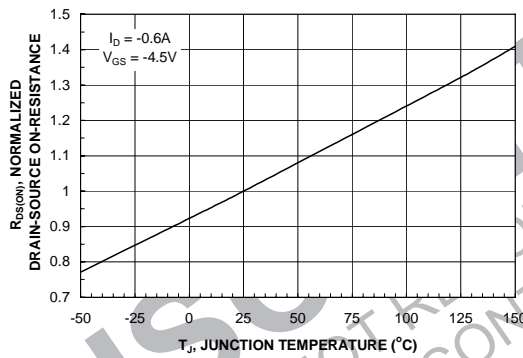Drain Current and Gate Voltage.

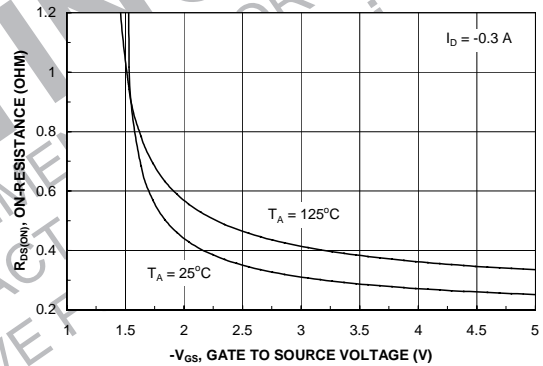Figure 3. On-Resistance Variation with
Temperature.

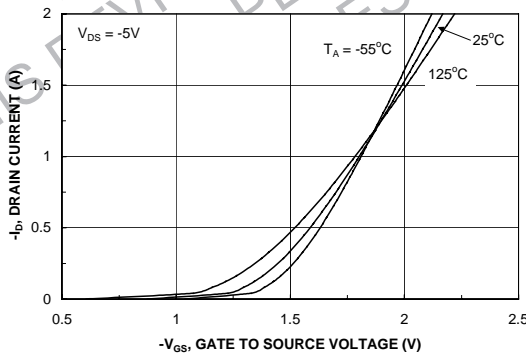Figure 4. On-Resistance Variation with
Gate-to-Source Voltage.

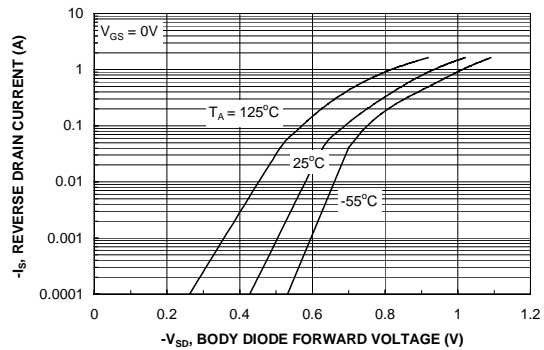Figure 5. Transfer Characteristics.

Figure 6. Body Diode Forward Voltage Variation
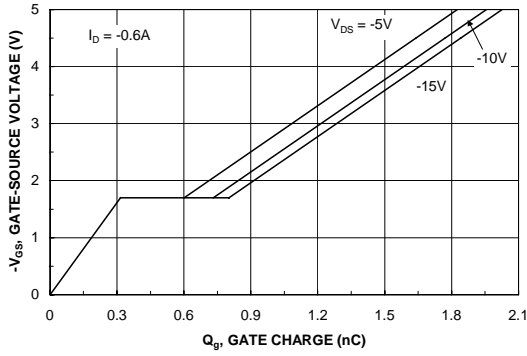with Source Current and Temperature.

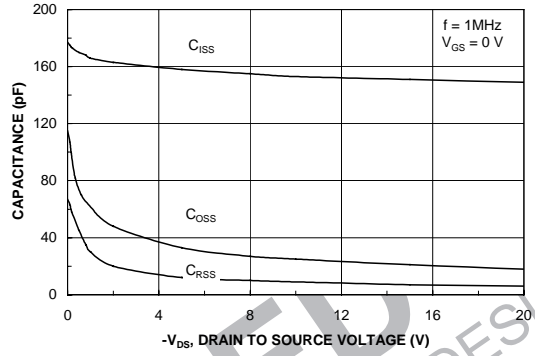## Typical Characteristics

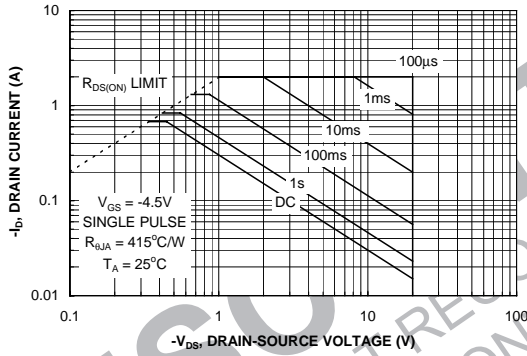

Figure 7. Gate Charge Characteristics.

Figure 8. Capacitance Characteristics.

Figure 9. Maximum Safe Operating Area.
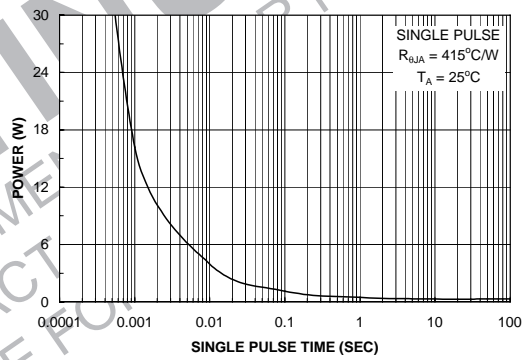
Figure 10. Single Pulse Maximum Power Dissipation.
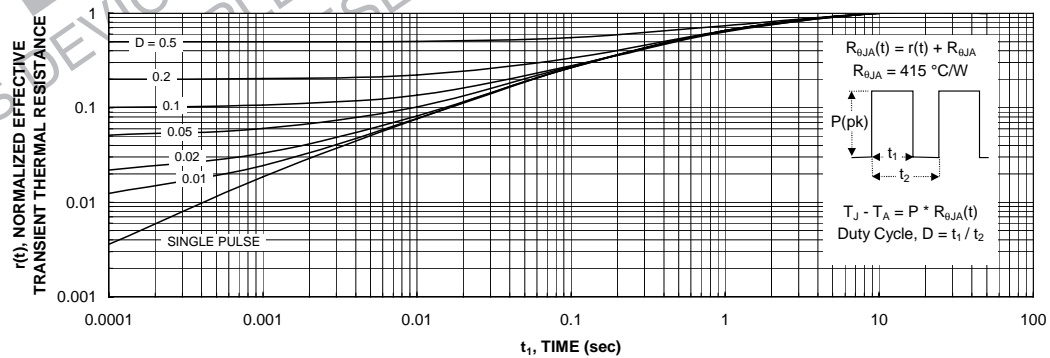
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1.
Transient thermal response will change depending on the circuit board design.

PUBLICATION ORDERING INFORMATION

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